

CONTENTS

PREFACE	xiii
1. INTRODUCTION TO CRYSTAL GROWTH METHODS	1
1.1. Introduction	1
1.2. The Literature of Crystal Growth	1
1.3. Solid Growth Processes	2
1.4. Melt Growth Processes	2
1.4.1. Normal freezing or directional freezing	2
1.5. Zone Refining	5
1.6. Vapour Growth Processes	6
1.7. Classification by α -factor	8
2. NUCLEATION AND GROWTH THEORY	12
2.1. Introduction	13
2.2. Crystal Models	13
2.2.1. Atomic bonding	13
2.2.2. Formation energy of clusters on a crystal plane	14
2.2.3. Surface diffusion	15
2.3. Supersaturation, Supercooling and Volume Energy	16
2.3.1. Growth from the vapour	16
2.3.2. Growth from the melt	18
2.3.3. Growth from solution	18
2.4. Three-dimensional Nucleation	19
2.4.1. Stability of small nuclei	19
2.4.2. The formation energy of liquid nuclei	20
2.4.3. The formation energy of crystalline nuclei	21
2.4.4. Nucleation rates	23
2.5. The Growth of Crystal Surfaces	26
2.5.1. Introduction	26
2.5.2. The equilibrium structure of surfaces	27
2.5.3. Two-dimensional nucleation and growth	27
2.5.4. Screw dislocation growth	31
2.5.5. Application to vapour, melt and solution growth	32
2.6. Material and Heat Flow in Crystal Growth	33
2.6.1. Growth from solution	33
2.6.2. Growth from the melt	34
2.6.3. Growth from the vapour	34
2.7. The Kinetic Generation of Crystal Forms	35
2.7.1. Whiskers	35
2.7.2. Needles and platelets	35
2.7.3. Flat faces	36
2.7.4. Equilibrium and characteristic habits	36
2.7.5. Dendrites	37

CONTENTS

3. THEORY OF INTERFACE STABILITY	40
3.1. Introduction	40
3.2. Constitutional Supercooling	43
3.3. The Dynamic Theory for Planar Interface Stability	50
3.3.1. Introduction	50
3.3.2. The use of the time dependent and time independent or Laplace diffusion equation	51
3.3.3. The effect of capillarity on the boundary conditions	54
3.3.4. The boundary conditions and solution for δ	57
3.3.5. Qualitative discussion of stability condition	59
3.3.6. Exact solutions for simplified problems	60
3.3.7. The effect of finite interface kinetics on interface stability	60
3.4. Melting Interfaces	61
3.4.1. The stability of a melting interface	61
3.4.2. Application to temperature gradient zone melting	67
3.5. The Stability of a Planar Freezing Interface under Convection	70
3.6. The Stability of Solid Spheres growing in Supercooled Liquids	77
3.6.1. Introduction	77
3.6.2. The unperturbed growth of the sphere with the time dependent diffusion equation (no kinetics or capillarity)	78
3.6.3. The Laplace diffusion equation for finding the growth of the sphere when capillarity and kinetics are included	80
3.6.4. The stability of a sphere growing in a slightly supercooled liquid	82
3.6.5. The stability of a sphere growing isothermally in a supersaturated medium	85
3.7. The Stability of a Solid Cylinder growing in a Supercooled Liquid	87
3.7.1. Introduction	87
3.7.2. The unperturbed growth of a cylinder including capillarity	90
3.7.3. The stability of a solid cylinder growing in a supercooled liquid	91
3.7.4. Perturbations with constant ω ; $k \gg 1$	94
3.7.5. Perturbations with $\omega = 0$ and $k \gg 1$	96
3.7.6. Experiments on ice cylinders growing in supercooled water	96
3.7.7. The stability of a cylinder growing in a slightly supersaturated medium	98
3.8. The Stability of Dendrites and Eutectics	98
3.9. Conclusions	100
4. ZONE MELTING AND APPLIED TECHNIQUES	104
4.1. Introduction	104
4.1.1. Brief description	104
4.1.2. Brief history	105
4.2. Theoretical Aspects of Zone Melting	106
4.2.1. The distribution coefficients	106
4.2.1.1. The equilibrium distribution coefficient	106
4.2.1.2. Interface distribution coefficient k^*	108
4.2.1.3. Effective distribution coefficient (k_{eff} or k)	109
4.2.1.4. Burton, Prim, and Slichter theory for k	110
4.2.2. Solute distribution in normal freezing processes	113
4.2.3. Solute distribution in zone melting	117
4.2.3.1. Single-pass distribution	117
4.2.3.2. Multipass distributions	121
4.2.3.3. Ultimate distributions	124
4.2.3.4. Cropping and ultimate distributions	125
4.2.3.5. Zone melting, variable k , and phase relationships	126
4.3. Factors Affecting the Practice of Zone Melting	132
4.3.1. The zone length	132
4.3.2. Zone traverse velocity	134
4.3.3. Temperature gradient at the solid/liquid interface	134
4.3.4. The degree of mixing in the liquid	134
4.3.5. Matter transport in zone melting	135

CONTENTS

4.4. Design and Choice of Zoning Equipment	137
4.4.1. Zoning in a container	137
4.4.2. Zone refining without containers	138
4.4.2.1. Electron beam heating	140
4.4.2.2. Induction heating	143
4.4.3. Traverse mechanisms	143
4.4.4. Design considerations for "ideal zones"	144
4.4.5. Stirring	145
4.5. Recent Advances in Zone-melting Techniques	146
4.5.1. Liquid encapsulation	146
4.5.2. Microscale zone melting	147
4.6. Non-conventional and Allied Techniques	148
4.6.1. Thin alloy zone techniques	148
4.6.1.1. TGZM	149
4.6.1.2. Direct current effects and zone melting	150
4.6.2. Solution zone refining	151
4.7. Conclusions	153
5. GROWTH OF SINGLE CRYSTALS OF GAAS IN BULK AND THIN FILM FORM	157
5.1. Introduction	157
5.2. Phase Equilibria and Vapour Pressures	158
5.3. Stoichiometry and Point Defects	161
5.4. Growth of Bulk Crystals	163
5.4.1. Czochralski techniques	163
5.4.1.1. Growth by liquid encapsulation	165
5.4.2. Vertical floating zone technique	165
5.4.3. Horizontal Bridgman technique	165
5.5. Epitaxial Films	167
5.5.1. Deposition by vapour transport	167
5.5.1.1. Chemical methods	167
5.5.1.2. Growth by transport of the elements	172
5.5.2. Deposition from the liquid phase	175
5.5.3. Electrical properties of epitaxial films	179
5.6. Crystallographic Defects	182
5.7. Conclusions	183
6. FLUX GROWTH	185
6.1. Introduction	185
6.2. Choice of a Flux	186
6.3. Phase Diagram Determination	188
6.4. The Growth Mechanism	191
6.5. Growth Stability	194
6.6. General Practical Considerations	197
6.7. Slow Cooling	198
6.8. Restriction of Nucleation	203
6.9. Seeded Growth	204
6.10. Solvent Evaporation	205
6.11. Temperature Gradient Methods	206
6.12. Other Methods	209
6.13. Imperfections	211
6.14. Conclusions	213
7. PRACTICAL ASPECTS OF FLUX GROWTH BY SPONTANEOUS NUCLEATION	217
7.1. Introduction: Versatility of the Method and its Limitations	217

CONTENTS

7.2.	Literature	218
7.3.	Equipment	221
7.3.1.	Rectangular muffle furnaces	221
7.3.2.	Adaptation of muffles for growth by flux evaporation	222
7.3.3.	Temperature measurement	222
7.3.4.	Chemicals	222
7.3.5.	Polarising microscope	223
7.3.6.	Analysis and synthesis	223
7.4.	Crucibles	223
7.4.1.	Specification	223
7.4.2.	Embedding crucibles in refractory brick	224
7.4.3.	Separation of crystals from flux and cleaning of crucibles	225
7.4.4.	Compatibility of fluxes with platinum	228
7.5.	Nucleation	230
7.5.1.	The density difference and its effect on solution and nucleation	231
7.5.2.	Volatility of the flux and its effect on nucleation	232
7.5.3.	Nucleation sites	232
7.5.4.	Dendritic growth following nucleation	233
7.5.5.	Seeded growth, and its complications	235
7.6.	Solute Diffusion and Crystal Growth	235
7.6.1.	Unstable growth and its results	235
7.6.2.	Stable growth	246
7.6.3.	Asymmetric heating and reduction of the rate of cooling	246
7.7.	Notes on Fluxes for Oxide Materials	246
7.7.1.	Fluxes containing bismuth	257
7.7.2.	Fluxes containing lead	262
7.7.3.	Fluxes containing compounds of Group I elements	265
7.7.4.	Fluxes containing compounds of Group II elements	266
7.7.5.	Miscellaneous fluxes	266
7.8.	Notes on Fluxes for Fluoride Materials—Chlorides and Fluorides	266
7.9.	Discussion	268
7.9.1.	Choice of flux	268
7.9.2.	Choice of chemicals for fluxed melts	270
7.9.3.	Methods of investigating the flux system	270
7.9.4.	Growth by flux evaporation compared with growth by slow cooling	271
7.9.5.	Additives to improve crystal size or quality	273
7.9.6.	Habit modification	273
7.9.7.	Cases with another substance as the primary phase	279
7.9.8.	Growth by flux evaporation under a controlled atmosphere	279
7.10.	Conclusion	279
8.	BULK CRYSTALLIZATION	289
8.1.	Supersaturation, Nucleation, and Crystal Growth	291
8.1.1.	Supersaturation and metastability	291
8.1.1.1.	Measurement of supersaturation	292
8.1.1.2.	Crystal yield	292
8.1.2.	Nucleation	293
8.1.3.	Crystal growth	296
8.1.3.1.	Overall growth rates	296
8.1.3.2.	Face growth rates	298
8.1.3.3.	Simultaneous nucleation and growth	299
8.1.3.4.	Expression of crystal growth rates	299
8.1.4.	Habit modification	300
8.1.4.1.	Industrial importance	302
8.1.5.	Mass transfer correlations	302
8.1.5.1.	Films and boundary layers	303
8.2.	Crystallization Methods and Equipment	305

CONTENTS

8.2.1.	Cooling crystallizers	305
8.2.2.	Controlled crystallization	306
8.2.3.	Evaporating and vacuum crystallizers	311
8.3.	Design and Operation of Crystallizers	316
8.3.1.	Crystallizer selection	316
8.3.2.	Scale-up and operating problems	317
8.3.3.	Modes of operation	319
8.3.4.	Concept of the population balance	320
8.3.4.1.	Crystal size distributions	322
8.3.5.	Applications of the population balance	323
9.	CREATION, MEASUREMENT, AND CONTROL OF CRYSTAL GROWTH ENVIRONMENT	326
9.1.	Introduction	326
9.1.1.	General remarks on instrumentation	326
9.1.2.	Parameters pertinent to measurement and control	327
9.2.	Temperature	328
9.2.1.	Method of heating	328
9.2.1.1.	Flame heating	329
9.2.1.2.	Electrical resistance heating	329
9.2.1.3.	High frequency heating	332
9.2.1.4.	Electron beam heating	336
9.2.1.5.	Plasma heating	339
9.2.1.6.	High intensity arcs	342
9.2.1.7.	Radiation imaging	345
9.2.1.8.	Thermal transfer	347
9.2.2.	Temperature measurement	347
9.2.2.1.	Expansion thermometry	350
9.2.2.2.	Resistance thermometry	351
9.2.2.3.	Thermocouple thermometry	356
9.2.2.4.	Radiation thermometry	359
9.2.2.5.	Other less widely known thermometries	365
9.2.3.	Temperature control	365
9.2.3.1.	Systems description of control mechanisms	367
9.2.3.2.	Elements of a control system and controller actions	368
9.2.3.3.	Methods of temperature control	373
9.2.3.4.	Common control elements in temperature control	373
9.2.3.5.	Temperature control in crystal growth	377
9.3.	Atmosphere	379
9.3.1.	Vacuum techniques	379
9.3.1.1.	Design of vacuum systems	380
9.3.1.2.	Measurement and control of vacuum	384
9.3.2.	High pressure techniques	388
9.3.3.	Dynamic atmospheres	388
9.4.	Container Materials	389
9.4.1.	General considerations	389
9.4.2.	Maintenance of containers	391
9.5.	Growth Velocity	391
9.5.1.	Macroscopic growth velocity	391
9.5.2.	Microgrowth fluctuations	392
9.6.	Conclusion	392
10.	GROWTH FROM THE VAPOUR PHASE	397
10.1.	Introduction	397
10.2.	Basis of Vapour Growth	397
10.3.	Physical Transport Techniques	400

CONTENTS

10.3.1. Hot filament and crucible sources	400
10.3.2. Cold crucible techniques	401
10.3.3. Flash evaporation	402
10.3.4. Molecular beam techniques	404
10.3.5. Growth of bulk crystals by physical transport	405
10.4. Chemical Transport Techniques	407
10.4.1. Chemical transport	407
10.4.2. Chemical vapour deposition	411
10.4.2.1. Hydride pyrolysis and halide reduction	412
10.4.2.2. Transfer reactions	414
10.5. Nucleation and Subsequent Growth of Epitaxial Layers	416
10.5.1. Nucleation	416
10.5.2. Post-nucleation growth in homo-epitaxial systems	418
10.5.3. Post-nucleation growth in hetero-epitaxial systems	420
10.5.4. Electrical properties of epitaxial layers	423
10.6. Summary and Conclusions	424
11. MOLTEN METAL SOLUTION GROWTH	427
11.1. Introduction	427
11.2. Phase Relationships	433
11.3. Kinetics	441
11.4. Methods of Molten Metal Solution Growth	447
11.4.1. Apparatus and methods for solution growth (SG)	448
11.4.1.1. Methods of SG involving temperature variation	448
11.4.1.2. Methods of SG involving a change in solution composition	451
11.4.2. Apparatus and methods for epitaxial growth (EP)	452
11.4.2.1. Liquid-phase epitaxy	453
11.4.2.2. Solution regrowth, alloying and alloy etching	464
11.4.2.3. Transient-mode liquid epitaxy	465
11.4.2.4. Isothermal solution mixing	465
11.4.2.5. The capillary liquid film technique	466
11.4.2.6. Czochralski growth from solution	467
11.4.2.7. Thin alloy zone crystallization	467
11.5. Properties of Semiconductors grown from Molten Metal Solution	469
11.5.1. Gallium arsenide	471
11.5.2. Gallium phosphide	476
11.5.3. Mixed-crystal compounds, especially $\text{Al}_x\text{Ga}_{(1-x)}\text{As}$	479
12. CRYSTAL PULLING	497
12.1. Introduction	497
12.2. Melts	500
12.3. Crucibles	501
12.4. Methods of Heating and Control	504
12.5. Seeding	508
12.6. Protective Atmospheres	509
12.7. Pull and Rotation Rates	510
12.8. Doping	512
12.9. Afterheaters	515
12.10. Examples of Typical Growth Conditions	518
13. METHODS OF GROWING CRYSTALS UNDER PRESSURE	521
13.1. Introduction	521
13.2. Resistance Heater Methods	522
13.2.1. Bridgman growth under high inert gas pressure	522
13.2.2. The capillary-tipped ampoule method for ZnTe	526

CONTENTS

13.2.3. The "soft ampoule" method	527
13.2.4. Preparing II-VI compounds from the pure elements	528
13.3. Induction Heater Methods	530
13.3.1. Vertical and horizontal Bridgman method in unsupported quartz ampoules	530
13.3.2. Vertical Bridgman growth in pressure-relieved ampoules	533
13.3.3. Czochralski-type pulling under pressure	539
13.4. Crystal Growth using Liquid Encapsulation (L.E.)	542
13.4.1. Czochralski pulling	542
13.4.2. Liquid encapsulation Bridgman growth	549
13.4.3. Liquid encapsulation zone leveling	549
13.5. Outlook: New Methods	554
13.5.1. Issuing phosphorus vapor into the melt	554
13.5.2. Continuous liquid phase epitaxy growth	554
13.6. Summary and Conclusions	555
14. CRYSTAL GROWTH FROM AQUEOUS SOLUTIONS	557
14.1. Growth Techniques	557
14.2. Crystal Phases	559
14.3. Equipment for Crystal Growth	560
14.3.1. Falling temperature technique	560
14.3.2. Constant temperature technique	561
14.3.3. Evaporation technique	563
14.3.4. Hydrothermal technique	564
14.4. Crystals grown Hydrothermally	566
14.4.1. Advantages of hydrothermal growth	566
14.4.2. Hydrothermal growth of α -quartz	567
14.4.3. Other crystals grown hydrothermally	570
14.5. Crystal Morphology and Growth Rate	570
14.6. Crystal Defects	574
15. DENDRITIC GROWTH	576
15.1. Introduction	576
15.2. Consequences of Dendritic Growth	581
15.2.1. Morphology	581
15.2.2. Crystal defects	581
15.2.3. Solute segregation	581
15.2.4. Void formation	584
15.2.5. Crystal multiplication	585
15.3. Instabilities that cause Dendritic Growth	586
15.4. "Steady-state" Dendritic Growth Velocity	587
15.4.1. Elementary treatment	588
15.4.2. Improvements to this elementary treatment	591
15.5. Experimental Data and Comparison with the Theoretical Predictions	594
15.5.1. Dendrite arm spacing	596
15.6. Appendix	598
16. LIQUID CRYSTALS	601
16.1. Introduction	601
16.1.1. Amphiphilic compounds or amphiphiles	601
16.1.2. Non-amphiphilic compounds or non-amphiphiles	602
16.1.3. A note on the historical origins of the subject	604
16.2. Thermotropic Liquid Crystals formed by Pure Non-Amphiphilic Compounds	605
16.2.1. Detection of liquid crystal transitions	607
16.2.2. Optical microscopy	609
16.2.3. Cholesteric liquid crystals	611

CONTENTS

16.2.4. Molecular structure and the properties of liquid crystals	612
16.3. Lyotropic Liquid Crystals formed by Amphiphilic Compounds	616
16.3.1. S_{1c} phase	620
16.3.2. Multicomponent systems	622
16.4. The Cholesteric Mesophase in Solutions of Polypeptides	622
16.5. Liquid Crystals in Biological Systems	623
16.6. Applications of Thermotropic Liquid Crystals	625
16.6.1. Gas-liquid chromatography	625
16.6.2. Nuclear magnetic resonance spectroscopy	625
16.6.3. Electron spin resonance spectroscopy	626
16.6.4. Surface thermography	626
16.6.5. Display devices	627
16.6.6. The guest-host interaction	628
16.6.7. Storage devices	628
17. ASSESSMENT OF CRYSTALLINE PERFECTION	632
17.1. Introduction	632
17.2. Volume, Area, Line, and Point Defects	633
17.3. Threshold Concentrations of Defects in Crystals	637
17.4. Methods for Detecting Structural Imperfections	638
17.4.1. Optical methods	638
17.4.2. Transmission electron microscopy	640
17.4.3. X-ray topography	649
17.4.4. Scanning electron microscopy	653
SUBJECT INDEX	666
COMPOUND INDEX	669